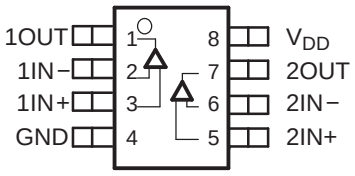
WIDE-BANDWIDTH HIGH-OUTPUT-DRIVE SINGLE-SUPPLY OPERATIONAL AMPLIFIER

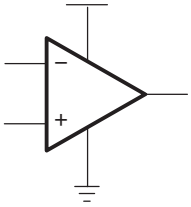
FEATURES

- **Qualified for Automotive Applications**
- **Wide Bandwidth . . . 10 MHz**
- **High-Output Drive**
  - **I_{OH} . . . 57 mA at V_{DD} – 1.5 V**
  - **I_{OL} . . . 55 mA at 0.5 V**
- **High Slew Rate**
  - **SR+ . . . 16 V/μs**
  - **SR– . . . 19 V/μs**
- **Wide Supply Range . . . 4.5 V to 16 V**
- **Supply Current . . . 1.9 mA/Channel**
- **Ultralow Power Shutdown Mode I_{DD} . . . 125 mA/Channel**
- **Low Input Noise Voltage . . . 7 nV/$\sqrt{Hz}$**
- **Input Offset Voltage . . . 60 μV**
- **Small 8-Pin SOIC Package**

TLC072
D PACKAGE
(TOP VIEW)



Operational Amplifier



DESCRIPTION/ORDERING INFORMATION

The first members of TI's new BiMOS general-purpose operational amplifier family are the TLC07x. The BiMOS family concept is simple: provide an upgrade path for BiFET users who are moving away from dual-supply to single-supply systems and demand higher AC and dc performance. With performance rated from 4.5 V to 16 V across commercial (0°C to 70°C) and an extended industrial temperature range (–40°C to 125°C), BiMOS suits a wide range of audio, automotive, industrial and instrumentation applications. Familiar features like offset nulling pins enable higher levels of performance in a variety of applications.

Developed in TI's patented LBC3 BiCMOS process, the new BiMOS amplifiers combine a very high input impedance low-noise CMOS front end with a high-drive bipolar output stage, thus providing the optimum performance features of both. AC performance improvements over the TL07x BiFET predecessors include a bandwidth of 10 MHz (an increase of 300%) and voltage noise of 7 nV/$\sqrt{Hz}$ (an improvement of 60%). DC improvements include a factor of 4 reduction in input offset voltage down to 1.5 mV (maximum) in the standard grade, and a power supply rejection improvement of greater than 40 dB to 130 dB. Added to this list of impressive features is the ability to drive ±50-mA loads comfortably from an ultrasmall-footprint MSOP PowerPAD™ package, which positions the TLC07x as the ideal high-performance general-purpose operational amplifier family.

ORDERING INFORMATION(1)

T_A	PACKAGE(2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 125°C	SOIC – D	Reel of 2500	TLC072QDRQ1	TC072Q

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

V_{DD}	Supply voltage(2)	17 V
V_{ID}	Differential input voltage range	$\pm V_{DD}$
	Continuous total power dissipation	See Dissipation Ratings Table
T_A	Operating free-air temperature range	–40°C to 125°C
T_J	Maximum virtual-junction temperature	150°C
T_{stg}	Storage temperature range	–65°C to 150°C
T_{lead}	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values, except differential voltages, are with respect to GND .

DISSIPATION RATINGS

PACKAGE	θ_{JC} (°C/W)	θ_{JA} (°C/W)	$T_A \leq 25°C$ POWER RATING
D	38.3	176	710 mW

RECOMMENDED OPERATING CONDITIONS

			MIN	MAX	UNIT
V_{DD}	Supply voltage	Single supply	4.5	16	V
		Split supply	±2.25	±8	
V_{ICR}	Common-mode input voltage		+0.5	V_{DD} – 0.8	V
T_A	Operating free-air temperature		–40	125	°C

ELECTRICAL CHARACTERISTICS

V_{DD} = 5 V, at specified free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A (1)	MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	V_{DD} = 5 V, V_{IC} = 2.5 V, V_O = 2.5 V, R_S = 50 Ω		25°C		390	1900	µV
				Full range			3000	
α_{VIO}	Temperature coefficient of input offset voltage	V_{DD} = 5 V, V_{IC} = 2.5 V, V_O = 2.5 V, R_S = 50 Ω		25°C		1.2		µV/°C
I_{IO}	Input offset current	V_{DD} = 5 V, V_{IC} = 2.5 V, V_O = 2.5 V, R_S = 50 Ω		25°C		0.7	50	pA
				Full range			700	
I_{IB}	Input bias current	V_{DD} = 5 V, V_{IC} = 2.5 V, V_O = 2.5 V, R_S = 50 Ω		25°C		1.5	50	pA
				Full range			700	
V_{ICR}	Common-mode input voltage	R_S = 50 Ω		25°C	0.5 to 4.2			V
				Full range	0.5 to 4.2			
V_{OH}	High-level output voltage	V_{IC} = 2.5 V	I_{OH} = –1 mA	25°C	4.1	4.3		V
				Full range	3.9			
			I_{OH} = –20 mA	25°C	3.7	4		
				Full range	3.5			
			I_{OH} = –35 mA	25°C	3.4	3.8		
				Full range	3.2			
			I_{OH} = –50 mA	25°C	3.2	3.6		
				Full range	3			
V_{OL}	Low-level output voltage	V_{IC} = 2.5 V	I_{OL} = 1 mA	25°C		0.18	0.25	V
				Full range			0.35	
			I_{OL} = 20 mA	25°C		0.35	0.39	
				Full range			0.45	
			I_{OL} = 35 mA	25°C		0.43	0.55	
				Full range			0.7	
			I_{OL} = 50 mA	25°C		0.48	0.63	
				Full range			0.7	
I_{OS}	Short-circuit output current	Sourcing		25°C		100		mA
		Sinking		25°C		100		
I_O	Output current	V_{OH} = 1.5 V from positive rail		25°C		57		mA
		V_{OL} = 0.5 V from negative rail		25°C		55		
A_{VD}	Large-signal differential voltage amplification	$V_{O(PP)}$ = 3 V, R_L = 10 kΩ		25°C	100	120		dB
				Full range	100			
$r_{i(d)}$	Differential input resistance			25°C		1000		GΩ
C_{IC}	Common-mode input capacitance	f = 10 kHz		25°C		22.9		pF
z_O	Closed-loop output impedance	f = 10 kHz, A_V = 10		25°C		0.25		Ω
CMRR	Common-mode rejection ratio	V_{IC} = 1 to 3 V, R_S = 50 Ω		25°C	80	95		dB
				Full range	80			
k_{SVR}	Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V_{DD} = 4.5 V to 16 V, V_{IC} = V_{DD}/2, No load		25°C	80	100		dB
				Full range	80			
I_{DD}	Supply current (per channel)	V_O = 2.5 V, No load		25°C		1.9	2.5	mA
				Full range			3.5	

(1) Full range is –40°C to 125°C.

OPERATING CHARACTERISTICS

V_{DD} = 5 V, at specified free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A (1)	MIN	TYP	MAX	UNIT
SR+	Positive slew rate at unity gain	$V_{O(PP)}$ = 0.8 V, C_L = 50 pF, R_L = 10 kΩ		25°C	10	16		V/µs
				Full range	9.5			
SR–	Negative slew rate at unity gain	$V_{O(PP)}$ = 0.8 V, C_L = 50 pF, R_L = 10 kΩ		25°C	12.5	19		V/µs
				Full range	10			
V_n	Equivalent input noise voltage	f = 100 Hz		25°C		12		$\frac{nV}{\sqrt{Hz}}$
		f = 1 kHz				7		
I_n	Equivalent input noise current	f = 1 kHz		25°C		0.6		$\frac{fA}{\sqrt{Hz}}$
THD + N	Total harmonic distortion plus noise	$V_{O(PP)}$ = 3 V, R_L = 10 kΩ and 250 Ω, f = 1 kHz	A_V = 1	25°C		0.002		%
			A_V = 10			0.012		
			A_V = 100			0.085		
GBWP	Gain-bandwidth product	f = 10 kHz, R_L = 10 kΩ		25°C		10		MHz
t_s	Settling time	$V_{(STEP)PP}$ = 1 V, A_V = –1, C_L = 10 pF, R_L = 10 kΩ	0.1%	25°C		0.18		µs
			0.01%			0.39		
		$V_{(STEP)PP}$ = 1 V, A_V = –1, C_L = 47 pF, R_L = 10 kΩ	0.1%			0.18		
			0.01%			0.39		
ϕ_m	Phase margin	R_L = 10 kΩ	C_L = 50 pF	25°C		32		°
			C_L = 0 pF			40		
G_m	Gain margin	R_L = 10 kΩ	C_L = 50 pF	25°C		2.2		dB
			C_L = 0 pF			3.3		

(1) Full range is –40°C to 125°C.

ELECTRICAL CHARACTERISTICS

V_{DD} = 12 V, at specified free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A (1)	MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	V_{DD} = 12 V, V_{IC} = 6 V, V_O = 6 V, R_S = 50 Ω		25°C		390	1900	μV
				Full range			3000	
α_{VIO}	Temperature coefficient of input offset voltage	V_{DD} = 12 V, V_{IC} = 6 V, V_O = 6 V, R_S = 50 Ω		25°C		1.2		μV/°C
I_{IO}	Input offset current	V_{DD} = 12 V, V_{IC} = 6 V, V_O = 6 V, R_S = 50 Ω		25°C		0.7	50	pA
				Full range			700	
I_{IB}	Input bias current	V_{DD} = 12 V, V_{IC} = 6 V, V_O = 6 V, R_S = 50 Ω		25°C		1.5	50	pA
				Full range			700	
V_{ICR}	Common-mode input voltage	R_S = 50 Ω		25°C	0.5 to 11.2			V
				Full range	0.5 to 11.2			
V_{OH}	High-level output voltage	V_{IC} = 6 V	I_{OH} = –1 mA	25°C	11.1	11.2		V
				Full range	11			
			I_{OH} = –20 mA	25°C	10.8	109		
				Full range	10.7			
			I_{OH} = –35 mA	25°C	10.6	10.7		
				Full range	10.3			
			I_{OH} = –50 mA	25°C	10.4	10.5		
				Full range	10.3			
V_{OL}	Low-level output voltage	V_{IC} = 6 V	I_{OL} = 1 mA	25°C		0.17	0.25	V
				Full range			0.35	
			I_{OL} = 20 mA	25°C		0.35	0.45	
				Full range			0.5	
			I_{OL} = 35 mA	25°C		0.4	0.52	
				Full range			0.6	
			I_{OL} = 50 mA	25°C		0.45	0.6	
				Full range			0.65	
I_{OS}	Short-circuit output current	Sourcing		25°C		150		mA
		Sinking		25°C		150		
I_O	Output current	V_{OH} = 1.5 V from positive rail		25°C		57		mA
		V_{OL} = 0.5 V from negative rail		25°C		55		
A_{VD}	Large-signal differential voltage amplification	$V_{O(PP)}$ = 8 V, R_L = 10 kΩ		25°C	120	140		dB
				Full range	120			
$r_{i(d)}$	Differential input resistance			25°C		1000		GΩ
C_{IC}	Common-mode input capacitance	f = 10 kHz		25°C		21.6		pF
z_O	Closed-loop output impedance	f = 10 kHz, A_V = 10		25°C		0.25		Ω
CMRR	Common-mode rejection ratio	V_{IC} = 1 to 10 V, R_S = 50 Ω		25°C	80	100		dB
				Full range	80			
k_{SVR}	Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V_{DD} = 4.5 V to 16 V, V_{IC} = V_{DD}/2, No load		25°C	80	100		dB
				Full range	80			
I_{DD}	Supply current (per channel)	V_O = 7.5 V, No load		25°C		2.1	2.9	mA
				Full range			3.5	

(1) Full range is –40°C to 125°C.

OPERATING CHARACTERISTICS

V_{DD} = 12 V, at specified free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A (1)	MIN	TYP	MAX	UNIT
SR+	Positive slew rate at unity gain	$V_{O(PP)}$ = 2 V, C_L = 50 pF, R_L = 10 kΩ		25°C	10	16		V/µs
				Full range	9.5			
SR–	Negative slew rate at unity gain	$V_{O(PP)}$ = 2 V, C_L = 50 pF, R_L = 10 kΩ		25°C	12.5	19		V/µs
				Full range	10			
V_n	Equivalent input noise voltage	f = 100 Hz		25°C		12		$\frac{nV}{\sqrt{Hz}}$
		f = 1 kHz				7		
I_n	Equivalent input noise current	f = 1 kHz		25°C		0.6		$\frac{fA}{\sqrt{Hz}}$
THD + N	Total harmonic distortion plus noise	$V_{O(PP)}$ = 8 V, R_L = 10 kΩ and 250 Ω, f = 1 kHz	A_V = 1	25°C		0.002		%
			A_V = 10			0.005		
			A_V = 100			0.022		
GBWP	Gain-bandwidth product	f = 10 kHz, R_L = 10 kΩ		25°C		10		MHz
t_s	Settling time	$V_{(STEP)PP}$ = 1 V, A_V = –1, C_L = 10 pF, R_L = 10 kΩ	0.1%	25°C		0.17		µs
			0.01%			0.22		
		$V_{(STEP)PP}$ = 1 V, A_V = –1, C_L = 47 pF, R_L = 10 kΩ	0.1%			0.17		
			0.01%			0.29		
ϕ_m	Phase margin	R_L = 10 kΩ	C_L = 50 pF	25°C		37		°
			C_L = 0 pF			42		
G_m	Gain margin	R_L = 10 kΩ	C_L = 50 pF	25°C		3.1		dB
			C_L = 0 pF			4		

(1) Full range is –40°C to 125°C.

TYPICAL CHARACTERISTICS

Table 1. Table of Graphs

			FIGURE
V_{IO}	Input offset voltage	vs Common-mode input voltage	1, 2
I_{IO}	Input offset current	vs Free-air temperature	3, 4
I_{IB}	Input bias current	vs Free-air temperature	3, 4
V_{OH}	High-level output voltage	vs High-level output current	5, 7
V_{OL}	Low-level output voltage	vs Low-level output current	6, 8
Z_o	Output impedance	vs Frequency	9
I_{DD}	Supply current	vs Supply voltage	10
PSRR	Power supply rejection ratio	vs Frequency	11
CMRR	Common-mode rejection ratio	vs Frequency	12
V_n	Equivalent input noise voltage	vs Frequency	13
$V_{O(PP)}$	Peak-to-peak output voltage	vs Frequency	14, 15
	Crosstalk	vs Frequency	16
	DIfferential voltage gain	vs Frequency	17, 18
	Phase	vs Frequency	17, 18
ϕ_m	Phase margin	vs Load capacitance	19, 20
	Gain margin	vs Load capacitance	21, 22
	Gain-bandwidth product	vs Supply voltage	23
SR	Slew rate	vs Supply voltage	24
		vs Free-air temperature	25, 26
THD + N	Total harmonic distortion plus noise	vs Frequency	27, 28
		vs Peak-to-peak output voltage	29, 30
	Large-signal follower pulse response		31, 32
	Small-signal follower pulse response		33
	Large-signal inverting pulse response		34, 35
	Small-signal inverting pulse response		36

INPUT OFFSET VOLTAGE
vs
COMMON-MODE INPUT VOLTAGE

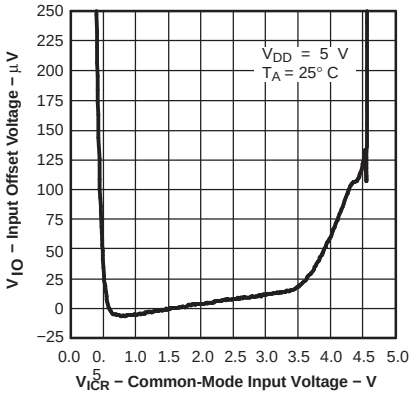


Figure 1.

INPUT OFFSET VOLTAGE
vs
COMMON-MODE INPUT VOLTAGE

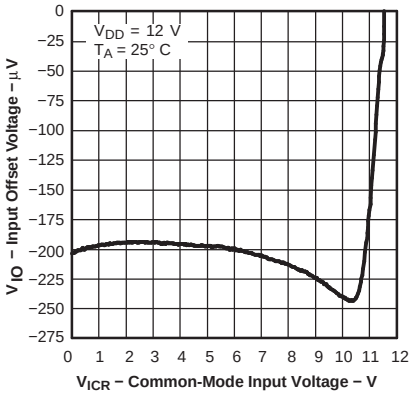


Figure 2.

INPUT BIAS CURRENT AND
INPUT OFFSET CURRENT
vs
FREE-AIR TEMPERATURE

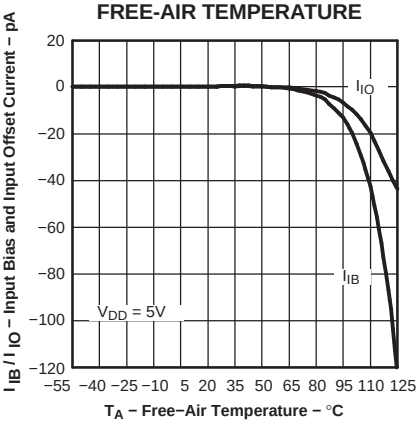


Figure 3.

INPUT BIAS CURRENT AND
INPUT OFFSET CURRENT
vs
FREE-AIR TEMPERATURE

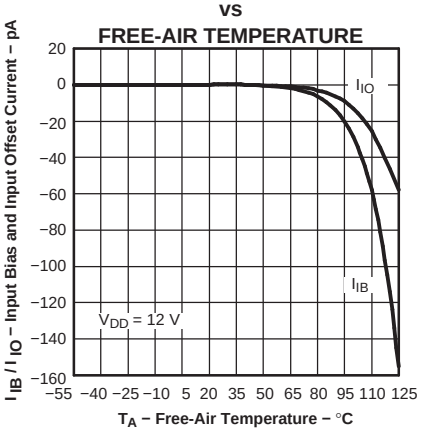


Figure 4.

HIGH-LEVEL OUTPUT VOLTAGE
vs
HIGH-LEVEL OUTPUT CURRENT

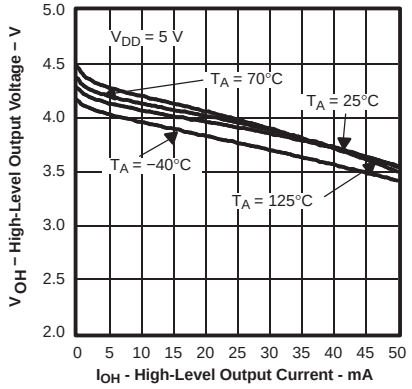


Figure 5.

LOW-LEVEL OUTPUT VOLTAGE
vs
LOW-LEVEL OUTPUT CURRENT

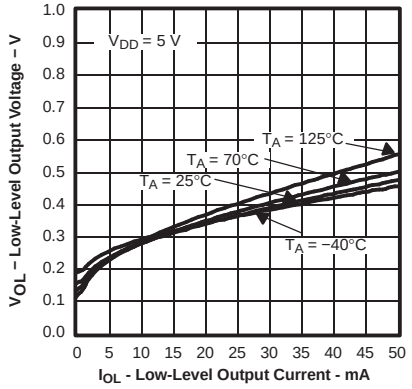


Figure 6.

HIGH-LEVEL OUTPUT VOLTAGE
vs
HIGH-LEVEL OUTPUT CURRENT

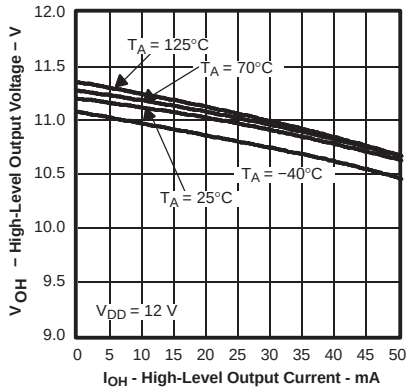


Figure 7.

LOW-LEVEL OUTPUT VOLTAGE
vs
LOW-LEVEL OUTPUT CURRENT

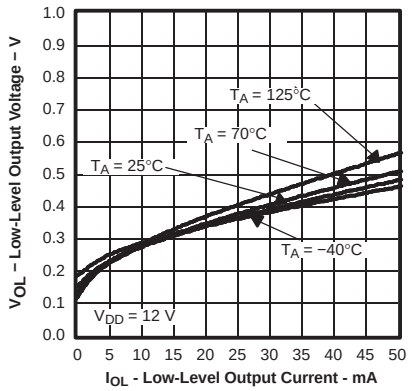


Figure 8.

OUTPUT IMPEDANCE
vs
FREQUENCY

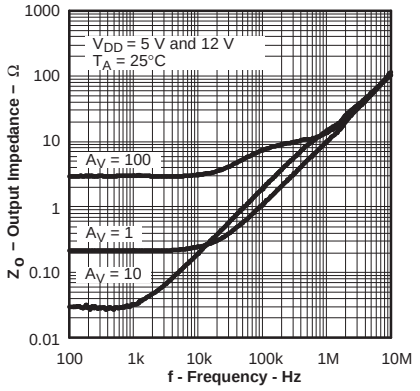


Figure 9.

SUPPLY CURRENT vs SUPPLY VOLTAGE

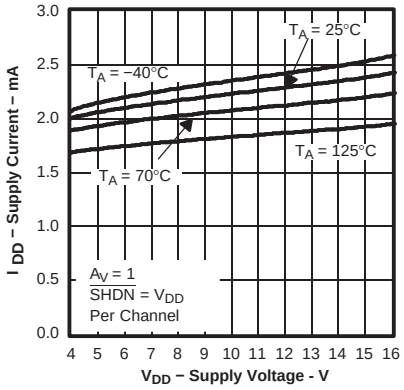


Figure 10.

POWER SUPPLY REJECTION RATIO vs FREQUENCY

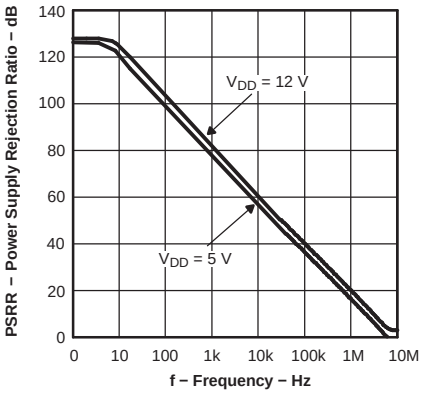


Figure 11.

COMMON-MODE REJECTION RATIO vs FREQUENCY

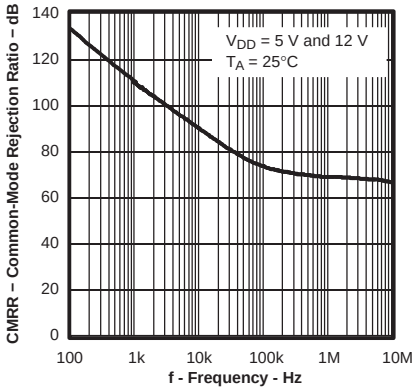


Figure 12.

EQUIVALENT INPUT NOISE VOLTAGE vs FREQUENCY

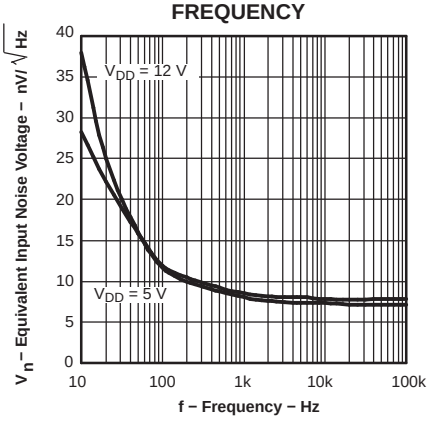


Figure 13.

PEAK-TO-PEAK OUTPUT VOLTAGE vs FREQUENCY

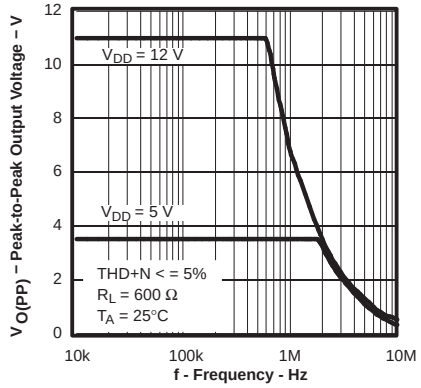


Figure 14.

PEAK-TO-PEAK OUTPUT VOLTAGE vs FREQUENCY

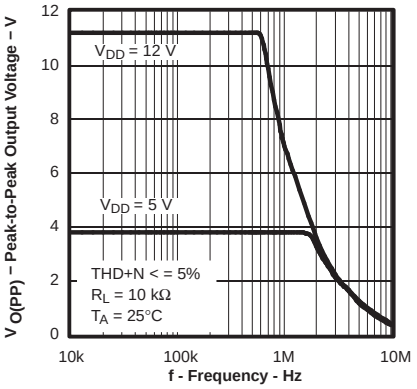


Figure 15.

CROSSTALK vs FREQUENCY

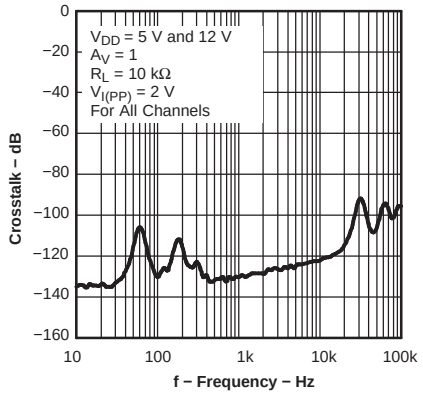


Figure 16.

DIFFERENTIAL VOLTAGE GAIN AND PHASE
vs
FREQUENCY

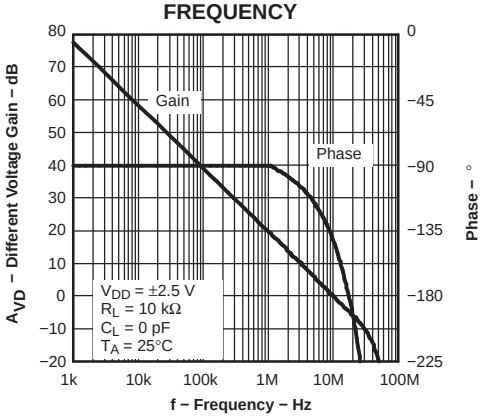


Figure 17.

DIFFERENTIAL VOLTAGE GAIN AND PHASE
vs
FREQUENCY

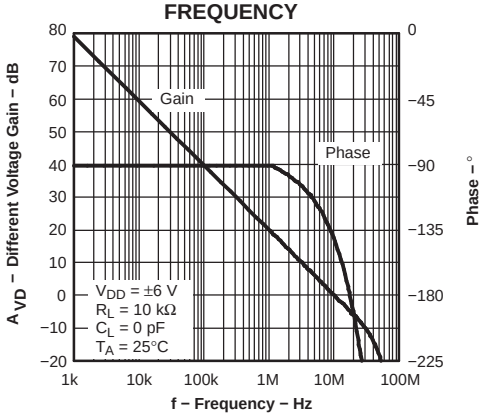


Figure 18.

PHASE MARGIN
vs
LOAD CAPACITANCE

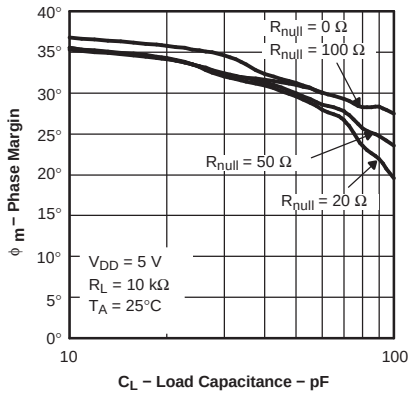


Figure 19.

PHASE MARGIN
vs
LOAD CAPACITANCE

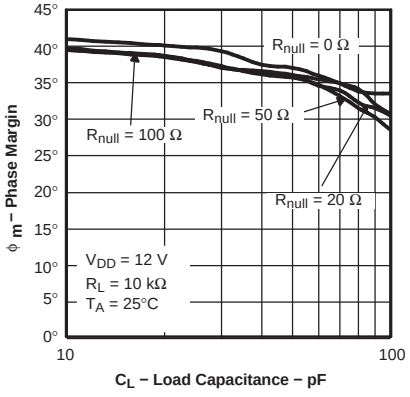


Figure 20.

GAIN MARGIN
vs
LOAD CAPACITANCE

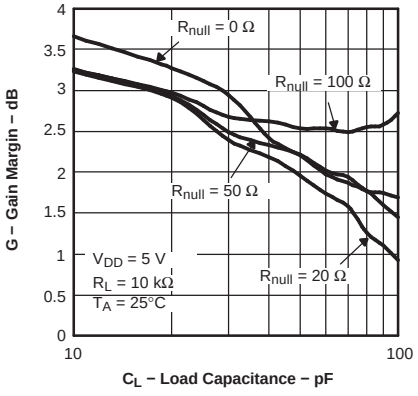


Figure 21.

GAIN MARGIN
vs
LOAD CAPACITANCE

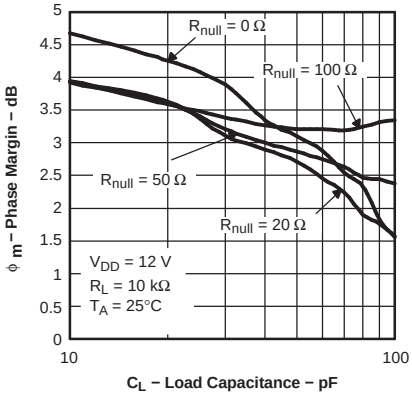


Figure 22.

GAIN BANDWIDTH PRODUCT
vs
SUPPLY VOLTAGE

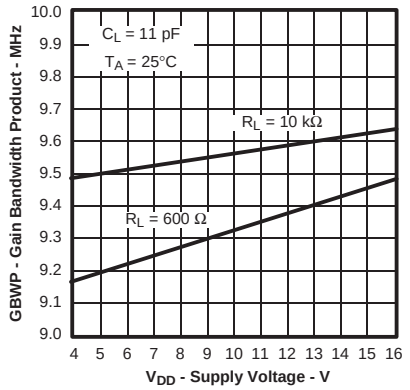


Figure 23.

SLEW RATE
vs
SUPPLY VOLTAGE

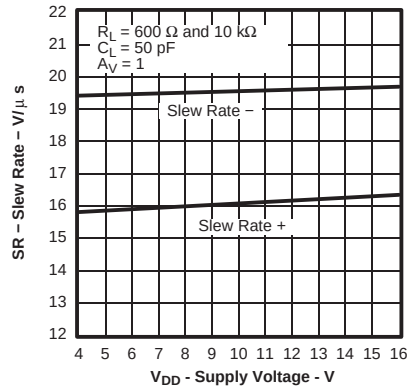


Figure 24.

SLEW RATE vs FREE-AIR TEMPERATURE

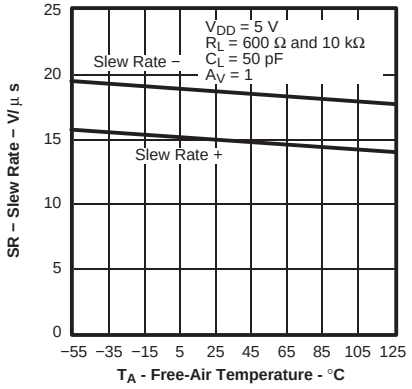


Figure 25.

SLEW RATE vs FREE-AIR TEMPERATURE

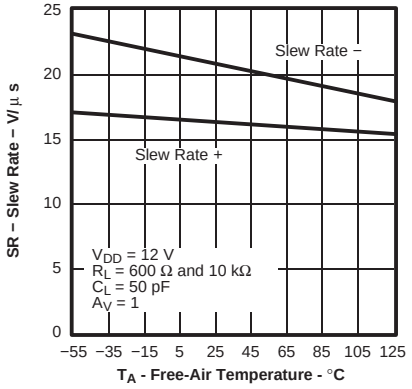


Figure 26.

TOTAL HARMONIC DISTORTION PLUS NOISE vs FREQUENCY

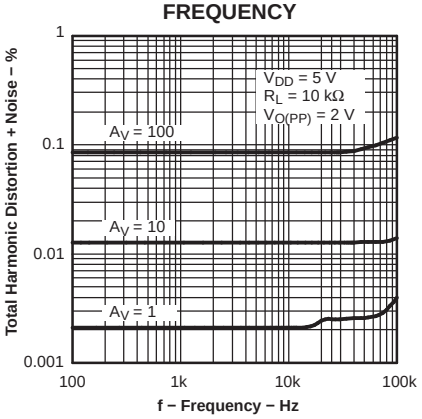


Figure 27.

TOTAL HARMONIC DISTORTION PLUS NOISE vs FREQUENCY

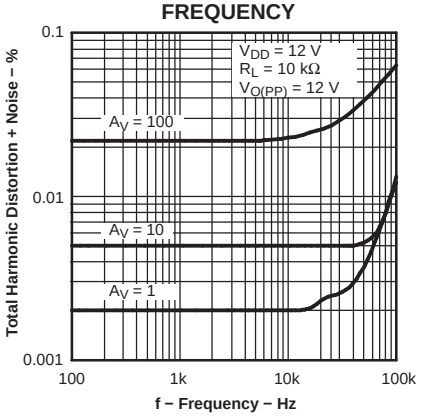


Figure 28.

TOTAL HARMONIC DISTORTION PLUS NOISE vs PEAK-TO-PEAK OUTPUT VOLTAGE

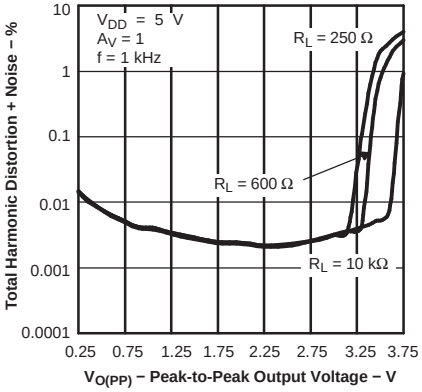


Figure 29.

TOTAL HARMONIC DISTORTION PLUS NOISE vs PEAK-TO-PEAK OUTPUT VOLTAGE

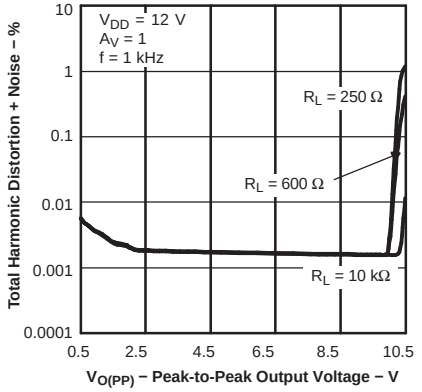


Figure 30.

LARGE SIGNAL FOLLOWER PULSE RESPONSE

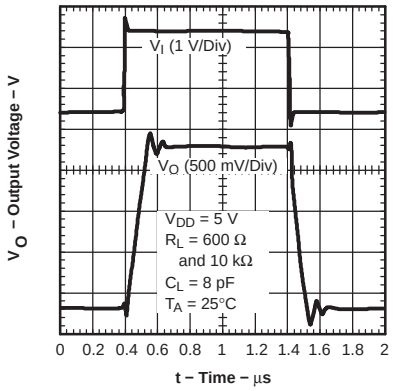


Figure 31.

LARGE SIGNAL FOLLOWER PULSE RESPONSE

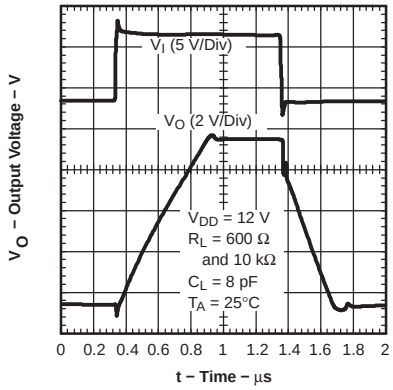


Figure 32.

SMALL SIGNAL FOLLOWER PULSE RESPONSE

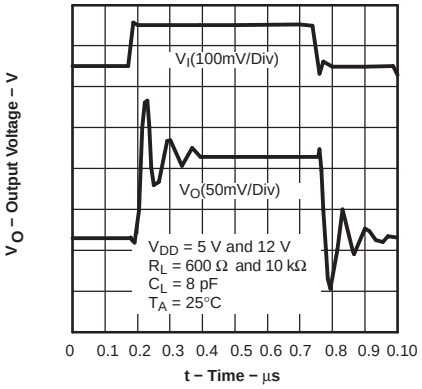


Figure 33.

LARGE SIGNAL INVERTING PULSE RESPONSE

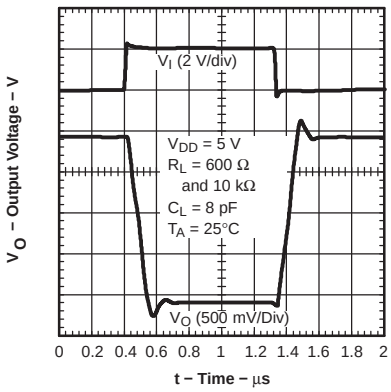


Figure 34.

LARGE SIGNAL INVERTING PULSE RESPONSE

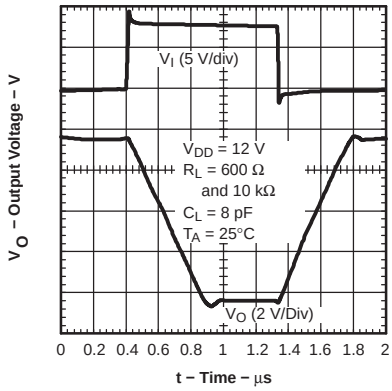


Figure 35.

SMALL SIGNAL INVERTING PULSE RESPONSE

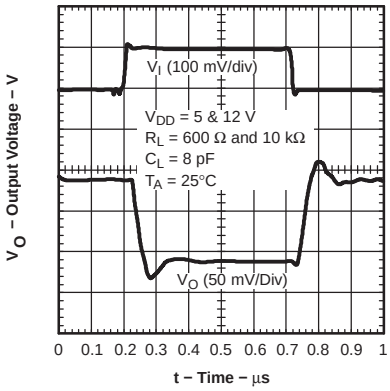


Figure 36.

PARAMETER MEASUREMENT INFORMATION

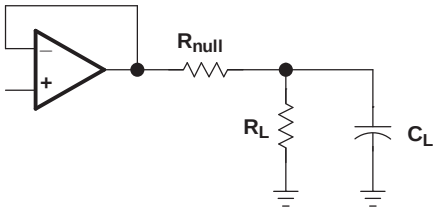


Figure 37. Input Offset Voltage Null Circuit

APPLICATION INFORMATION

Driving a Capacitive Load

When the amplifier is configured in this manner, capacitive loading directly on the output decreases the device's phase margin, leading to high-frequency ringing or oscillations. Therefore, for capacitive loads of greater than 10 pF, it is recommended that a resistor be placed in series (R_{NULL}) with the output of the amplifier, as shown in Figure 38. A minimum value of 20 Ω should work well for most applications.

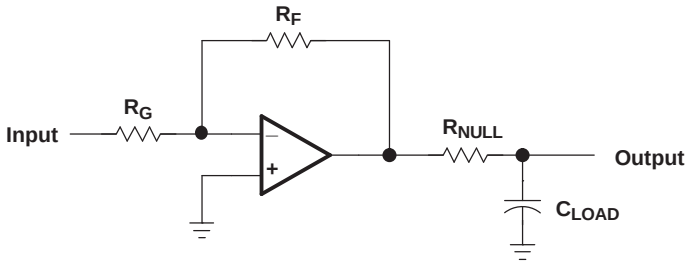
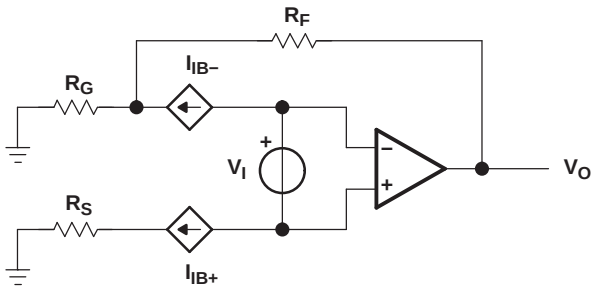


Figure 38. Driving a Capacitive Load

Offset Voltage

The output offset voltage (V_{OO}) is the sum of the input offset voltage (V_{IO}) and both input bias currents (I_{IB}) times the corresponding gains. The following schematic and formula (see Figure 39) can be used to calculate the output offset voltage:



$$V_{OO} = V_{IO}\left(1 + \left(\frac{R_F}{R_G}\right)\right) \pm I_{IB+} R_S \left(1 + \left(\frac{R_F}{R_G}\right)\right) \pm I_{IB-} R_F$$

Figure 39. Output Offset Voltage Model

High-Speed CMOS Input Amplifiers

The TLC072 is a high-speed low-noise CMOS input operational amplifier that has an input capacitance of the order of 20 pF. Any resistor used in the feedback path adds a pole in the transfer function equivalent to the input capacitance multiplied by the combination of source resistance and feedback resistance. For example, a gain of –10, a source resistance of 1 kΩ, and a feedback resistance of 10 kΩ add an additional pole at approximately 8 MHz. This is more apparent with CMOS amplifiers than bipolar amplifiers due to their greater input capacitance.

This is of little consequence on slower CMOS amplifiers, as this pole normally occurs at frequencies above their unity-gain bandwidth. However, the TLC07x with its 10-MHz bandwidth means that this pole normally occurs at frequencies where there is on the order of 5-dB gain left and the phase shift adds considerably.

The effect of this pole is the strongest with large feedback resistances at small closed loop gains. As the feedback resistance is increased, the gain peaking increases at a lower frequency and the 180° phase shift crossover point also moves down in frequency, decreasing the phase margin.

For the TLC072, the maximum feedback resistor recommended is 5 kΩ; larger resistances can be used but a capacitor in parallel with the feedback resistor is recommended to counter the effects of the input capacitance pole.

The TLC072 with a 1-V step response has an 80% overshoot with a natural frequency of 3.5 MHz when configured as a unity gain buffer and with a 10-kΩ feedback resistor. By adding a 10-pF capacitor in parallel with the feedback resistor, the overshoot is reduced to 40% and eliminates the natural frequency, resulting in a much faster settling time (see Figure 40). The 10-pF capacitor was chosen for convenience only.

Load capacitance had little effect on these measurements due to the excellent output drive capability of the TLC072.

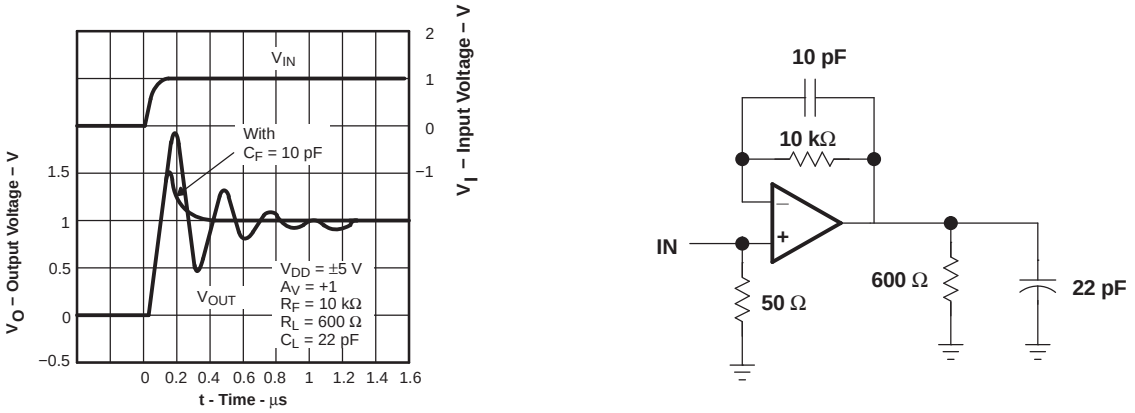


Figure 40. 1-V Step Response

General Configurations

When receiving low-level signals, limiting the bandwidth of the incoming signals into the system is often required. The simplest way to accomplish this is to place an RC filter at the noninverting terminal of the amplifier (see Figure 41).

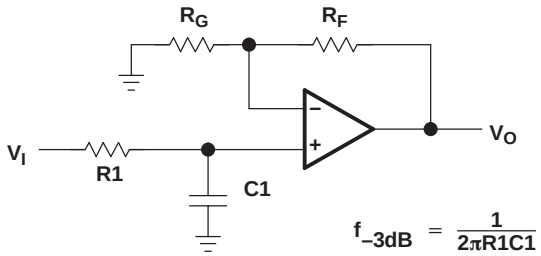


Figure 41. Single-Pole Low-Pass Filter

If even more attenuation is needed, a multiple pole filter is required. The Sallen-Key filter can be used for this task (see Figure 42). For best results, the amplifier should have a bandwidth that is 8 to 10 times the filter frequency bandwidth. Failure to do this can result in phase shift of the amplifier.

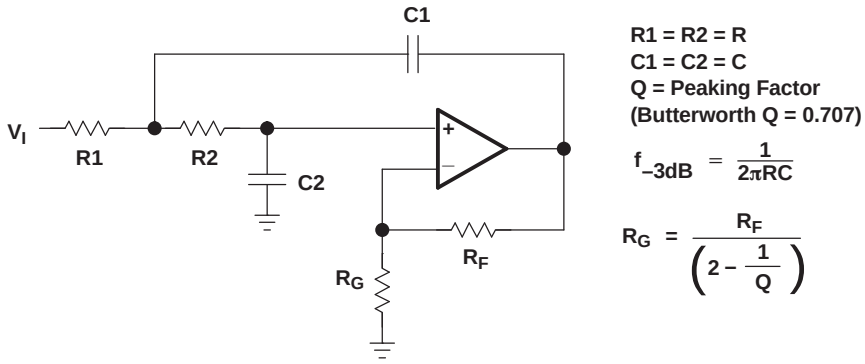


Figure 42. Two-Pole Low-Pass Sallen-Key Filter

Circuit Layout Considerations

To achieve the levels of high performance of the TLC072, follow proper printed-circuit board design techniques. A general set of guidelines is given in the following.

- Ground planes

  A ground plane should be used on the board to provide all components with a low inductive ground connection. However, in the areas of the amplifier inputs and output, the ground plane can be removed to minimize the stray capacitance.

- Proper power supply decoupling

  Use a 6.8-µF tantalum capacitor in parallel with a 0.1-µF ceramic capacitor on each supply terminal. It may be possible to share the tantalum among several amplifiers depending on the application, but a 0.1-µF ceramic capacitor should always be used on the supply terminal of every amplifier. In addition, the 0.1-µF capacitor should be placed as close as possible to the supply terminal. As this distance increases, the inductance in the connecting trace makes the capacitor less effective. The designer should strive for distances of less than 0.1 inch between the device power terminals and the ceramic capacitors.

- Sockets

  Sockets can be used but are not recommended. The additional lead inductance in the socket pins often leads to stability problems. Surface-mount packages soldered directly to the printed-circuit board is the best implementation.

- Short trace runs/compact part placements

  Optimum high performance is achieved when stray series inductance has been minimized. To realize this, the circuit layout should be made as compact as possible, thereby minimizing the length of all trace runs. Particular attention should be paid to the inverting input of the amplifier. Its length should be kept as short as possible. This will help to minimize stray capacitance at the input of the amplifier.

- Surface-mount passive components

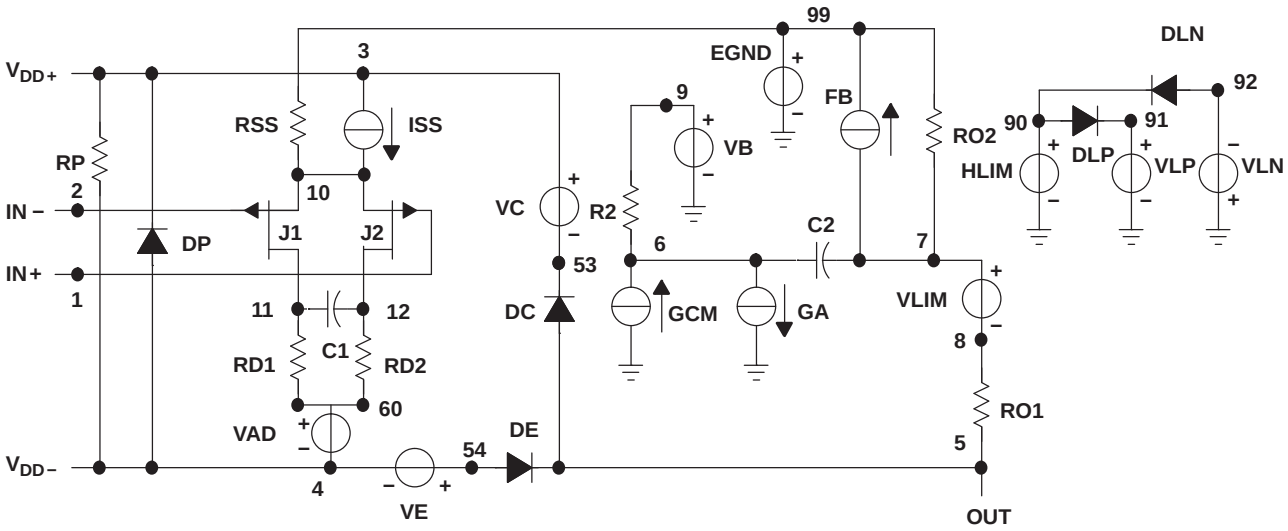
  Using surface-mount passive components is recommended for high performance amplifier circuits for several reasons. First, because of the extremely low lead inductance of surface-mount components, the problem with stray series inductance is greatly reduced. Second, the small size of surface-mount components naturally leads to a more compact layout thereby minimizing both stray inductance and capacitance. If leaded components are used, it is recommended that the lead lengths be kept as short as possible.

Macromodel Information

Macromodel information provided was derived using MicroSim Parts™, the model generation software used with MicroSim PSpice™. The Boyle macromodel(1) and subcircuit in Figure 43 are generated using the TLC07x typical electrical and operating characteristics at T_A = 25°C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

(1) G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers," *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).

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*DEVICE=TLC07X_5V, OPAMP, PJF, INT

* TLC07X − 5V operational amplifier "macromodel" subcircuit
* created using Parts release 8.0 on 12/16/99 at 08:38
* Parts is a MicroSim product.
*
* connections:              non-inverting input
*                           |  inverting input
*                           |  |  positive power supply
*                           |  |  |  negative power supply
*                           |  |  |  |  output
*                           |  |  |  |  |
.subckt TLC07X_5V  1 2 3 4 5
*
 c1     11  12  4.8697E−12
 c2     6   7   8.0000E−12
 css    10  99  4.0063E−12
 dc     5   53  dy
 de     54  5   dy
 dlp    90  91  dx
 dln    92  90  dx
 dp     4   3   dx
 egnd   99  0   poly(2) (3,0) (4,0) 0 .5 .5
 fb     7   99  poly(5) vb vc ve vlp vln 0 6.9132E6 −1E3 1E3
                6E6 −6E6
 ga     6   0   11  12 457.42E−6
 gcm    0   6   10  99 1.1293E−6
 iss    3   10  dc  183.67E−6
 ioff   0   6   dc  .806E−6
 hlim   90  0   vlim 1K
 j1     11  2   10  jx1
 j2     12  1   10  jx2
 r2     6   9       100.00E3
 rd1    4   11      2.1862E3
 rd2    4   12      2.1862E3
 ro1    8   5   10
 ro2    7   99  10
 rp     3   4       2.4728E3
 rss    10  99      1.0889E6
 vb     9   0   dc  0
 vc     3   53  dc  1.5410
 ve     54  4   dc  .84403
 vlim   7   8   dc  0
 vlp    91  0   dc  119
 vln    0   92  dc  119
.model  dx  D(Is=800.00E−18)
.model  dy  D(Is=800.00E−18 Rs=1m Cjo=10p)
.model  jx1 PJF(Is=117.50E−15 Beta=1.1391E−3  Vto=−1)
.model  jx2 PJF(Is=117.50E−15 Beta=1.1391E−3  Vto=−1)
.ends
```

Figure 43. Boyle Macromodel and Subcircuit

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLC072QDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TC072Q	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF TLC072-Q1 :

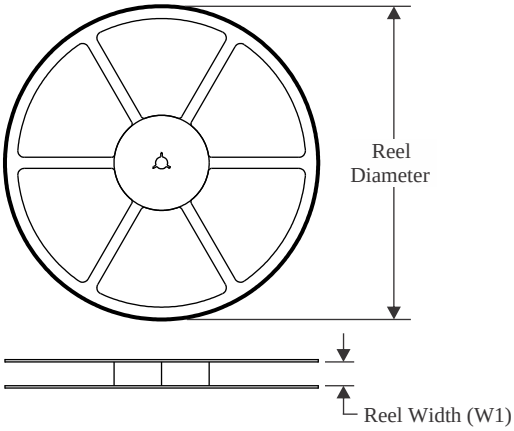
- Catalog: TLC072

NOTE: Qualified Version Definitions:

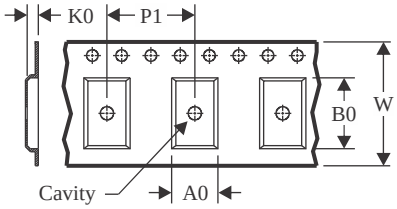
- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

REEL DIMENSIONS

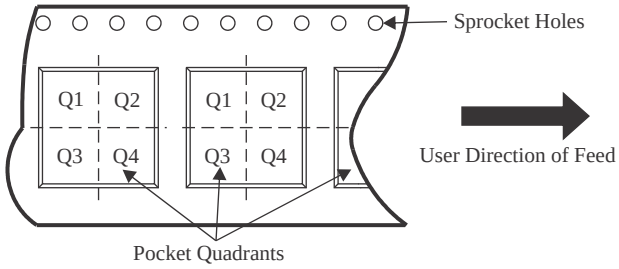


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

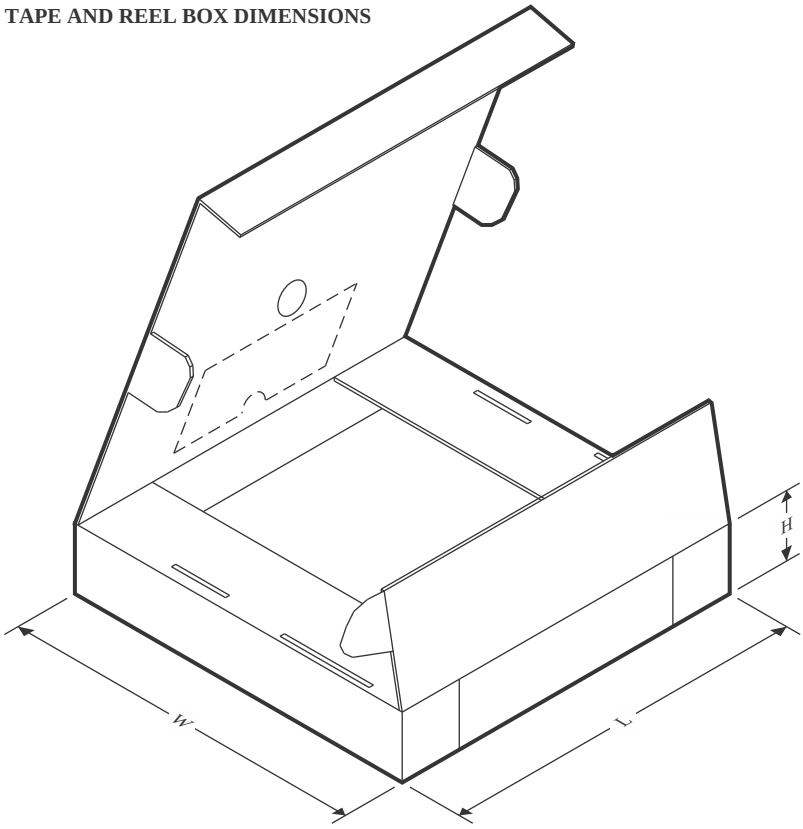
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

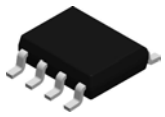
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC072QDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC072QDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC072QDRQ1	SOIC	D	8	2500	340.5	336.1	25.0
TLC072QDRQ1	SOIC	D	8	2500	350.0	350.0	43.0

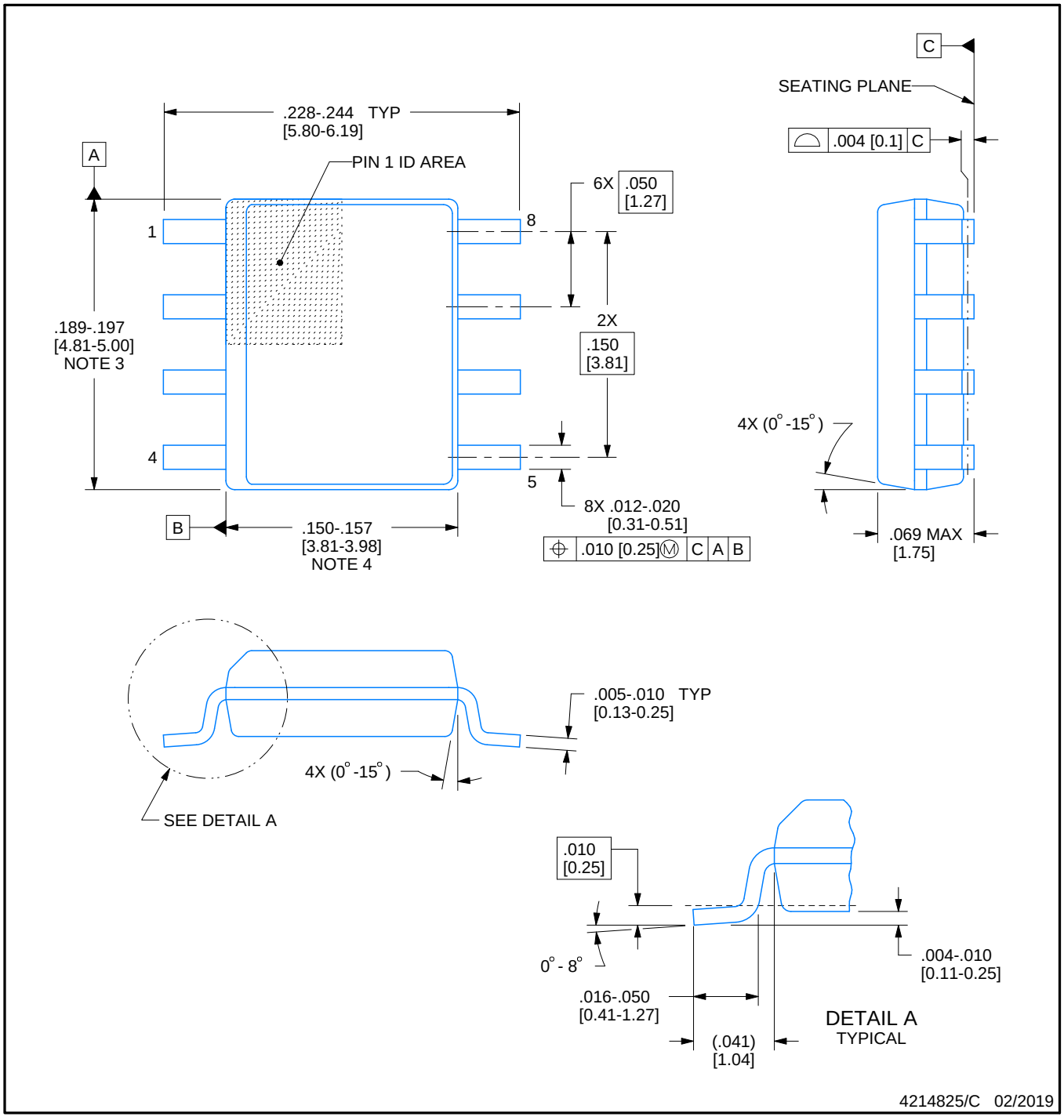


PACKAGE OUTLINE

D0008A

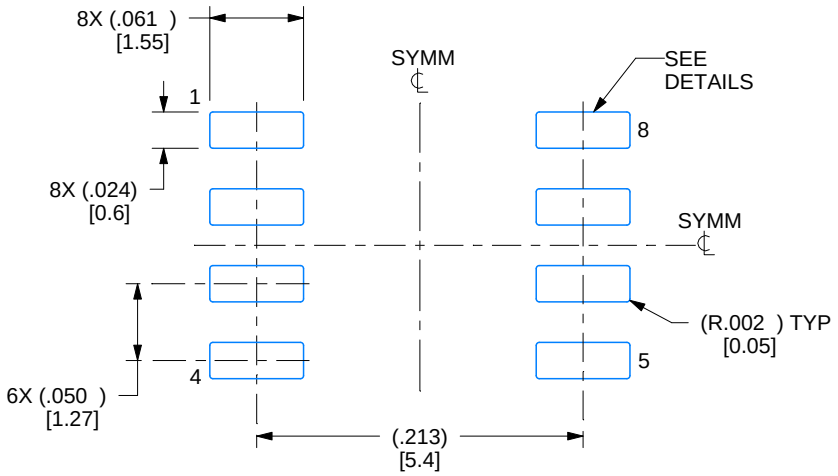
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

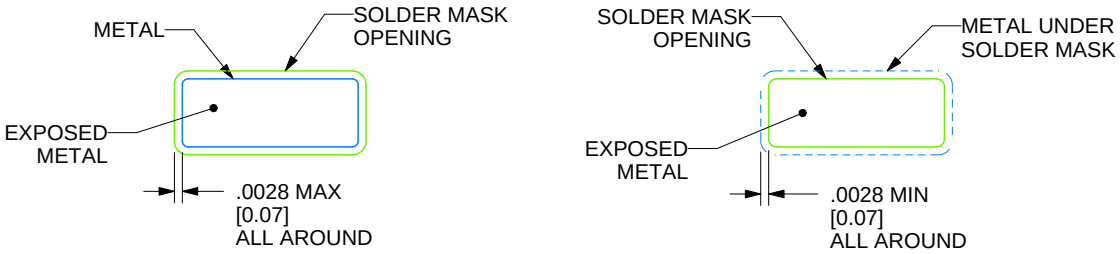


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

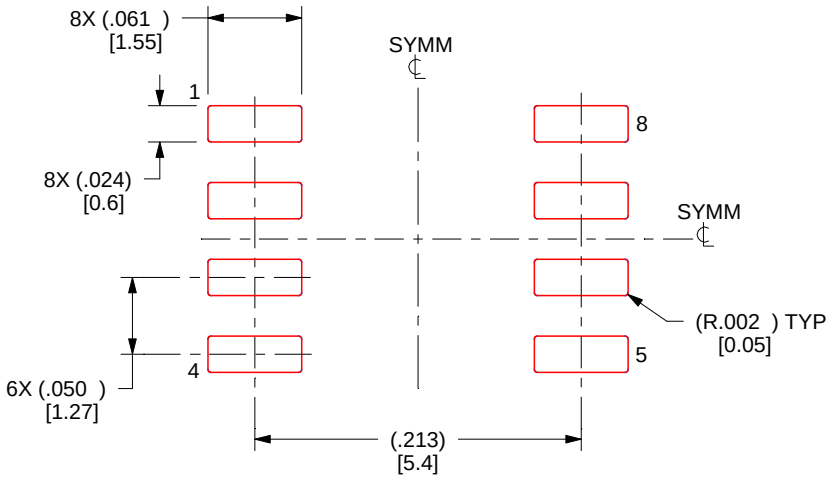
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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